Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of claims

Claims 1-5. (cancelled)

Claim 6. (previously presented) The method of claim 23, wherein:

said weight % of said nonaqueous solvent in said aqueous slurry/nonaqueous solvent mixture is increased until said aqueous slurry/nonaqueous solvent mixture is substantially free of said aqueous slurry.

Claim 7. (previously presented) The method of claim 25, wherein:

said nonaqueous solvent includes an amine.

Claim 8. (previously presented) The method of claim 25, wherein:

said nonaqueous solvent includes dimethylsulfoxide.

Claim 9. (previously presented) The method of claim 25, wherein:

said nonaqueous solvent includes N,N-propanalamide.

Claim 10. (previously presented) The method of claim 25, wherein:

said nonaqueous solvent includes analine.

Claim 11. (previously presented) The method of claim 25, wherein:

said nonaqueous solvent includes N,N-dimethlyanaline.

Claim 12. (cancelled)

Claim 13. (previously presented) A method of fabricating a semiconductor wafer, comprising:

(a) subjecting a front side of said semiconductor wafer to chemical mechanical polishing using an aqueous slurry; and

(b) disposing, a volume of nonaqueous liquid including a nonaqueous solvent onto said front side of said semiconductor wafer during said chemical mechanical polishing to rinse said semiconductor wafer,

wherein:

said nonaqueous solvent includes an amine.

Claims 14-20. (cancelled)

Claim 21. (previously presented) A method of fabricating a semiconductor wafer, comprising:

(a) mixing an aqueous slurry containing an abrasive material and a nonaqueous solvent in a mixing unit so as to create a first volume of an aqueous slurry/nonaqueous solvent mixture with a first weight % of said nonaqueous solvent prior to being disposed onto said semiconductor wafer;

(b) disposing said first volume of the aqueous slurry/nonaqueous solvent mixture containing an abrasive material onto said semiconductor wafer;

(c) polishing the semiconductor wafer with a polishing pad using said first volume;

(d) mixing said aqueous slurry containing an abrasive material and said nonaqueous solvent so as to create a second volume of an aqueous slurry/nonaqueous solvent mixture having a greater weight % of said nonaqueous solvent than said first weight % prior to being disposed onto said semiconductor wafer;

(e) disposing said second volume of said aqueous slurry/nonaqueous solvent mixture containing an abrasive material onto said semiconductor wafer; and

(f) polishing said semiconductor wafer using said second volume.

Claim 22. (currently amended) The method of claim 21, further comprising:

reducing the pressure between ~~of~~ said polishing pad and ~~on~~ said semiconductor wafer after disposing said first volume of said aqueous slurry/nonaqueous solvent mixture onto said semiconductor wafer and before completing disposing said second volume of said aqueous slurry/nonaqueous solvent mixture onto said semiconductor wafer.

Claim 23. (previously presented) The method of claim 21, wherein said disposing said second volume of aqueous slurry/nonaqueous solvent mixture further comprises:

disposing said second volume of aqueous slurry/nonaqueous solvent mixture during said polishing of said semiconductor wafer.

Claim 24. (previously presented) The method of claim 23, wherein mixing said second volume of an aqueous slurry/nonaqueous solvent mixture is performed at least partially simultaneously with disposing said first volume onto said semiconductor wafer, and mixing said second volume comprises:

controlling a flow of said nonaqueous solvent into said mixing unit.

Claim 25. (currently amended) A method of fabricating a semiconductor wafer, comprising:

(a) disposing a volume of an aqueous slurry containing an abrasive material onto a semiconductor wafer and polishing the semiconductor wafer with a polishing pad, said polishing pad in contact with said semiconductor wafer when said volume of aqueous slurry is disposed onto said semiconductor wafer; ~~and~~

(b) disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said semiconductor wafer to rinse the semiconductor wafer [[.]] ; and

(c) facilitating the advancement of the nonaqueous liquid into contact with the semiconductor wafer by reducing the pressure between ~~of~~ said polishing pad ~~on~~ and said semiconductor wafer prior to completing disposing the volume of nonaqueous liquid including the nonaqueous solvent onto said semiconductor

wafer.

Claim 26. (previously presented) The method of claim 13, further comprising:

reducing the pressure of a polishing pad on said front side of said semiconductor wafer prior to completing disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said front side of said semiconductor wafer.

Claim 27. (previously presented) The method of claim 26, wherein reducing the pressure further comprises reducing the pressure of said polishing pad on said semiconductor wafer during, and prior to completing, the disposing of the volume of nonaqueous liquid including the nonaqueous solvent onto said semiconductor wafer.

Claim 28 (currently amended) The method of claim 25, wherein step c) further comprises reducing the pressure of said polishing pad on said semiconductor wafer during~~, and prior to completing,~~ the disposing of the volume of nonaqueous liquid including the nonaqueous solvent onto said semiconductor wafer.